

Giovanni Isella

List of Publications by Year in descending order

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papers

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81900

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381
all docs

381
docs citations

381
times ranked

4623
citing authors

#	ARTICLE	IF	CITATIONS
1	Analysis of enhanced light emission from highly strained germanium microbridges. Nature Photonics, 2013, 7, 466-472.	31.4	367
2	Integrated germanium optical interconnects on silicon substrates. Nature Photonics, 2014, 8, 482-488.	31.4	196
3	Midinfrared Plasmon-Enhanced Spectroscopy with Germanium Antennas on Silicon Substrates. Nano Letters, 2015, 15, 7225-7231.	9.1	173
4	Scaling Hetero-Epitaxy from Layers to Three-Dimensional Crystals. Science, 2012, 335, 1330-1334.	12.6	149
5	Low-energy plasma-enhanced chemical vapor deposition for strained Si and Ge heterostructures and devices. Solid-State Electronics, 2004, 48, 1317-1323.	1.4	141
6	Germanium-based integrated photonics from near- to mid-infrared applications. Nanophotonics, 2018, 7, 1781-1793.	6.0	128
7	23 GHz Ge/SiGe multiple quantum well electro-absorption modulator. Optics Express, 2012, 20, 3219.	3.4	108
8	Very high hole mobilities in modulation-doped Ge quantum wells grown by low-energy plasma enhanced chemical vapor deposition. Applied Physics Letters, 2002, 80, 2922-2924.	3.3	100
9	Scattering mechanisms in high-mobility strained Ge channels. Applied Physics Letters, 2004, 84, 3058-3060.	3.3	93
10	Graded SiGe waveguides with broadband low-loss propagation in the mid infrared. Optics Express, 2018, 26, 870.	3.4	93
11	Ultralow dark current Ge/Si(100) photodiodes with low thermal budget. Applied Physics Letters, 2009, 94, .	3.3	89
12	Optical Spin Injection and Spin Lifetime in Ge Heterostructures. Physical Review Letters, 2012, 108, 156603.	7.8	89
13	Tunability of the dielectric function of heavily doped germanium thin films for mid-infrared plasmonics. Physical Review B, 2016, 94, .	3.2	86
14	Direct-Gap Gain and Optical Absorption in Germanium Correlated to the Density of Photoexcited Carriers, Doping, and Strain. Physical Review Letters, 2012, 109, 057402.	7.8	84
15	Raman spectroscopy determination of composition and strain in heterostructures. Materials Science in Semiconductor Processing, 2008, 11, 279-284.	4.0	78
16	Optical transitions in Ge/SiGe multiple quantum wells with Ge-rich barriers. Physical Review B, 2008, 78, .	3.2	73
17	Ultrafast nonlinear optical response of photoexcited Ge/SiGe quantum wells: Evidence for a femtosecond transient population inversion. Physical Review B, 2009, 79, .	3.2	73
18	A singlet-triplet hole spin qubit in planar Ge. Nature Materials, 2021, 20, 1106-1112.	27.5	73

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19	The thermoelectric properties of Ge/SiGe modulation doped superlattices. Journal of Applied Physics, 2013, 113, .	2.5	65
20	Phonon strain shift coefficients in Si _{1-x} Ge _x alloys. Journal of Applied Physics, 2008, 103, .	2.5	63
21	Excess carrier lifetimes in Ge layers on Si. Applied Physics Letters, 2014, 104, .	3.3	62
22	Quantum-confined Stark effect measurements in Ge/SiGe quantum-well structures. Optics Letters, 2010, 35, 2913.	3.3	61
23	Low-loss Ge-rich Si _{0.2} Ge _{0.8} waveguides for mid-infrared photonics. Optics Letters, 2017, 42, 105.	3.3	56
24	Unexpected Dominance of Vertical Dislocations in High-Misfit Ge/Si(001) Films and Their Elimination by Deep Substrate Patterning. Advanced Materials, 2013, 25, 4408-4412.	21.0	55
25	Optical Activation of Germanium Plasmonic Antennas in the Mid-Infrared. Physical Review Letters, 2016, 117, 047401.	7.8	55
26	Near infrared image sensor with integrated germanium photodiodes.. Journal of Applied Physics, 2011, 110, .	2.5	52
27	On-Chip Mid-Infrared Supercontinuum Generation from 3 to 13 μ m Wavelength. ACS Photonics, 2020, 7, 3423-3429.	6.6	52
28	Investigating the lateral motion of SiGe islands by selective chemical etching. Surface Science, 2006, 600, 2608-2613.	1.9	50
29	Characterization of Ge-on-Si virtual substrates and single junction GaAs solar cells. Semiconductor Science and Technology, 2006, 21, 775-780.	2.0	48
30	Room temperature photoluminescence of Ge multiple quantum wells with Ge-rich barriers. Applied Physics Letters, 2011, 98, 031106.	3.3	48
31	The cross-plane thermoelectric properties of p-Ge/Si _{0.5} Ge _{0.5} superlattices. Applied Physics Letters, 2013, 103, .	3.3	47
32	Spin voltage generation through optical excitation of complementary spin populations. Nature Materials, 2014, 13, 790-795.	27.5	46
33	Raman spectroscopy of Si _{1-x} Ge _x epilayers. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2005, 124-125, 127-131.	3.5	45
34	Effective mass in remotely doped Ge quantum wells. Applied Physics Letters, 2003, 82, 754-756.	3.3	44
35	Ge-rich graded-index Si _{1-x} Ge _x waveguides with broadband tight mode confinement and flat anomalous dispersion for nonlinear mid-infrared photonics. Optics Express, 2017, 25, 6561.	3.4	44
36	Self-aligned Ge and SiGe three-dimensional epitaxy on dense Si pillar arrays. Surface Science Reports, 2013, 68, 390-417.	7.2	43

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37	Plasmonic mid-infrared third harmonic generation in germanium nanoantennas. <i>Light: Science and Applications</i> , 2018, 7, 106.	16.6	42
38	Observation of Large Unidirectional Rashba Magnetoresistance in Ge(111). <i>Physical Review Letters</i> , 2020, 124, 027201.	7.8	42
39	On-chip Fourier-transform spectrometer based on spatial heterodyning tuned by thermo-optic effect. <i>Scientific Reports</i> , 2019, 9, 14633.	3.3	41
40	Polarization-dependent absorption in Ge/SiGe multiple quantum wells: Theory and experiment. <i>Physical Review B</i> , 2009, 79, .	3.2	39
41	Ge/SiGe multiple quantum well photodiode with 30 GHz bandwidth. <i>Applied Physics Letters</i> , 2011, 98, .	3.3	38
42	Analysis of Ge micro-cavities with in-plane tensile strains above 2 %. <i>Optics Express</i> , 2016, 24, 4365.	3.4	38
43	Ultra-wideband Ge-rich silicon germanium integrated Mach-Zehnder interferometer for mid-infrared spectroscopy. <i>Optics Letters</i> , 2017, 42, 3482.	3.3	38
44	Room temperature direct gap electroluminescence from Ge/Si _{0.15} Ge _{0.85} multiple quantum well waveguide. <i>Applied Physics Letters</i> , 2011, 99, .	3.3	37
45	Highly Mismatched, Dislocation-Free SiGe/Si Heterostructures. <i>Advanced Materials</i> , 2016, 28, 884-888.	21.0	37
46	Scanning X-ray strain microscopy of inhomogeneously strained Ge micro-bridges. <i>Journal of Synchrotron Radiation</i> , 2014, 21, 111-118.	2.4	37
47	CMOS-Compatible Bias-Tunable Dual-Band Detector Based on GeSn/Ge/Si Coupled Photodiodes. <i>ACS Photonics</i> , 2021, 8, 2166-2173.	6.6	36
48	Defect imaging of SiGe strain relaxed buffers grown by LEPECVD. <i>Materials Science in Semiconductor Processing</i> , 2006, 9, 802-805.	4.0	35
49	Structural characterization of thick, high-quality epitaxial Ge on Si substrates grown by low-energy plasma-enhanced chemical vapor deposition. <i>Journal of Electronic Materials</i> , 2003, 32, 976-980.	2.2	34
50	Heterojunction photodiodes fabricated from Ge/Si (1% ⁰) layers grown by low-energy plasma-enhanced CVD. <i>Semiconductor Science and Technology</i> , 2007, 22, S26-S28.	2.0	34
51	High temperature single photon emitter monolithically integrated on silicon. <i>Applied Physics Letters</i> , 2012, 100, .	3.3	34
52	Ge Crystals on Si Show Their Light. <i>Physical Review Applied</i> , 2014, 1, .	3.8	34
53	Nanocrystalline silicon films as multifunctional material for optoelectronic and photovoltaic applications. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2006, 134, 118-124.	3.5	32
54	Spin and energy relaxation in germanium studied by spin-polarized direct-gap photoluminescence. <i>Physical Review B</i> , 2013, 88, .	3.2	32

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55	Polarization dependence of quantum-confined Stark effect in Ge/SiGe quantum well planar waveguides. <i>Optics Letters</i> , 2011, 36, 1794.	3.3	31
56	Perfect crystals grown from imperfect interfaces. <i>Scientific Reports</i> , 2013, 3, 2276.	3.3	31
57	Benchmarking the Use of Heavily Doped Ge for Plasmonics and Sensing in the Mid-Infrared. <i>ACS Photonics</i> , 2018, 5, 3601-3607.	6.6	31
58	Voltage-tunable dual-band Ge/Si photodetector operating in VIS and NIR spectral range. <i>Optics Express</i> , 2019, 27, 8529.	3.4	31
59	Quantum-confined Stark effect at $1.3\ \mu\text{m}$ in Ge/Si _{0.35} Ge _{0.65} quantum-well structure. <i>Optics Letters</i> , 2012, 37, 3960.	3.3	29
60	Spin-Hall Voltage over a Large Length Scale in Bulk Germanium. <i>Physical Review Letters</i> , 2017, 118, 167402.	7.8	29
61	Thin SiGe virtual substrates for Ge heterostructures integration on silicon. <i>Journal of Applied Physics</i> , 2014, 115, .	2.5	28
62	Strong confinement-induced engineering of the g factor and lifetime of conduction electron spins in Ge quantum wells. <i>Nature Communications</i> , 2016, 7, 13886.	12.8	28
63	Optical properties of highly n-doped germanium obtained by <i>in situ</i> doping and laser annealing. <i>Journal Physics D: Applied Physics</i> , 2017, 50, 465103.	2.8	28
64	Nonlinear Properties of Ge-rich Si _{1-x} Ge _x Materials with Different Ge Concentrations. <i>Scientific Reports</i> , 2017, 7, 14692.	3.3	28
65	Room temperature laser operation of strained InGaAs/GaAs QW structure monolithically grown by MOVCD on LE-PECVD Ge _{0.5} Si virtual substrate. <i>Electronics Letters</i> , 2003, 39, 1658.	1.0	27
66	Advances Toward Ge/SiGe Quantum-Well Waveguide Modulators at $1.3\ \mu\text{m}$. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2014, 20, 33-39.	2.9	27
67	Recent progress in GeSi electro-absorption modulators. <i>Science and Technology of Advanced Materials</i> , 2014, 15, 014601.	6.1	27
68	Group-IV midinfrared plasmonics. <i>Journal of Nanophotonics</i> , 2015, 9, 093789.	1.0	27
69	Emission Engineering in Germanium Nanoresonators. <i>ACS Photonics</i> , 2015, 2, 53-59.	6.6	27
70	Electronic structure of epitaxial thin NiO(100) films grown on Ag(100): Towards a firm experimental basis. <i>Physical Review B</i> , 2001, 64, .	3.2	26
71	High mobility SiGe heterostructures fabricated by low-energy plasma-enhanced chemical vapor deposition. <i>Microelectronic Engineering</i> , 2004, 76, 279-284.	2.4	26
72	Strain-induced shift of phonon modes in alloys. <i>Materials Science in Semiconductor Processing</i> , 2006, 9, 541-545.	4.0	26

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73	Spin polarized photoemission from strained Ge epilayers. Applied Physics Letters, 2011, 98, .	3.3	26
74	GaAs/Ge crystals grown on Si substrates patterned down to the micron scale. Journal of Applied Physics, 2016, 119, .	2.5	26
75	Recent Progress on Ge/SiGe Quantum Well Optical Modulators, Detectors, and Emitters for Optical Interconnects. Photonics, 2019, 6, 24.	2.0	26
76	Structural characterization of nc-Si films grown by low-energy PECVD on different substrates. Applied Surface Science, 2008, 254, 2804-2808.	6.1	25
77	Fabrication of high efficiency III-V quantum nanostructures at low thermal budget on Si. Applied Physics Letters, 2009, 95, 241102.	3.3	25
78	Extending the emission wavelength of Ge nanopillars to 225 nm using silicon nitride stressors. Optics Express, 2015, 23, 18193.	3.4	25
79	Broadband integrated racetrack ring resonators for long-wave infrared photonics. Optics Letters, 2019, 44, 407.	3.3	25
80	10-Gb/s Ge/SiGe Multiple Quantum-Well Waveguide Photodetector. IEEE Photonics Technology Letters, 2011, 23, 1430-1432.	2.5	24
81	Patterning-induced strain relief in single lithographic SiGe nanostructures studied by nanobeam x-ray diffraction. Nanotechnology, 2012, 23, 155702.	2.6	24
82	Engineered Coalescence by Annealing 3D Ge Microstructures into High-Quality Suspended Layers on Si. ACS Applied Materials & Interfaces, 2015, 7, 19219-19225.	8.0	24
83	SiGe wet chemical etchants with high compositional selectivity and low strain sensitivity. Semiconductor Science and Technology, 2008, 23, 085021.	2.0	23
84	Raman efficiency in SiGe alloys. Physical Review B, 2010, 82, .	3.2	23
85	Spin band-gap renormalization and hole spin dynamics in Ge/SiGe quantum wells. Physical Review B, 2012, 85, .	3.2	23
86	Ge/SiGe superlattices for thermoelectric energy conversion devices. Journal of Materials Science, 2013, 48, 2829-2835.	3.7	23
87	Electro-refractive effect in Ge/SiGe multiple quantum wells. Applied Physics Letters, 2013, 102, .	3.3	23
88	Photoinduced inverse spin Hall effect in Pt/Ge(001) at room temperature. Applied Physics Letters, 2013, 102, .	3.3	23
89	Giant electro-optic effect in Ge/SiGe coupled quantum wells. Scientific Reports, 2015, 5, 15398.	3.3	23
90	Dynamics of Hole Singlet-Triplet Qubits with Large ΔE_{ST} -Factor Differences. Physical Review Letters, 2022, 128, 126803.	7.8	23

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91	Electronic and magnetic properties of the Co/Fe(001) interface and the role of oxygen. Physical Review B, 2000, 61, 15294-15301.	3.2	22
92	Giant dynamical Stark shift in germanium quantum wells. Applied Physics Letters, 2011, 98, .	3.3	22
93	Photoluminescence decay of direct and indirect transitions in Ge/SiGe multiple quantum wells. Journal of Applied Physics, 2012, 111, 013501.	2.5	22
94	Thermal transport through short-period SiGe nanodot superlattices. Journal of Applied Physics, 2014, 115, 044312.	2.5	22
95	Mid-infrared intersubband absorption from p-Ge quantum wells grown on Si substrates. Applied Physics Letters, 2016, 108, .	3.3	22
96	Imaging spin diffusion in germanium at room temperature. Physical Review B, 2017, 96, .	3.2	22
97	Direct gap related optical transitions in Ge/SiGe quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2009, 41, 972-975.	2.7	21
98	Si/SiGe quantum cascade superlattice designs for terahertz emission. Journal of Applied Physics, 2010, 107, 053109.	2.5	21
99	Strain relaxation of GaAs/Ge crystals on patterned Si substrates. Applied Physics Letters, 2014, 104, .	3.3	21
100	Prospects for SiGe thermoelectric generators. Solid-State Electronics, 2014, 98, 70-74.	1.4	21
101	Photon energy dependence of photo-induced inverse spin-Hall effect in Pt/GaAs and Pt/Ge. Applied Physics Letters, 2015, 106, .	3.3	21
102	Optical modulation in Ge-rich SiGe waveguides in the mid-infrared wavelength range up to 11 μm . Communications Materials, 2020, 1, .	6.9	21
103	Ge-rich graded SiGe waveguides and interferometers from 5 to 11 μm wavelength range. Optics Express, 2020, 28, 12771.	3.4	21
104	An experimental and theoretical investigation of a magnetically confined dc plasma discharge. Journal of Applied Physics, 2008, 104, .	2.5	20
105	Vertical arrays of nanofluidic channels fabricated without nanolithography. Lab on A Chip, 2009, 9, 1556.	6.0	19
106	Comparison of ultrafast carrier thermalization in $\text{Ga}_{1-x}\text{Si}_x$ quantum wells. Physical Review B, 2010, 81, .	3.2	19
107	1.55 μm direct bandgap electroluminescence from strained n-Ge quantum wells grown on Si substrates. Applied Physics Letters, 2012, 101, .	3.3	19
108	Experimental evaluation of the spin-Hall conductivity in Si-doped GaAs. Physical Review B, 2013, 88, .	3.2	19

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109	Quantum-confined direct-gap transitions in tensile-strained Ge/SiGe multiple quantum wells. Applied Physics Letters, 2011, 99, 031907.	3.3	18
110	Above-room-temperature photoluminescence from a strain-compensated Ge/Si _{0.15} Ge _{0.85} multiple-quantum-well structure. Applied Physics Letters, 2012, 100, .	3.3	18
111	3D heteroepitaxy of mismatched semiconductors on silicon. Thin Solid Films, 2014, 557, 42-49.	1.8	18
112	Spin-to-charge conversion for hot photoexcited electrons in germanium. Physical Review B, 2018, 97, .	3.2	18
113	Dislocation-Free SiGe/Si Heterostructures. Crystals, 2018, 8, 257.	2.2	18
114	On-chip infrared photonics with Si-Ge-heterostructures: What is next?. APL Photonics, 2022, 7, .	5.7	18
115	Epitaxial Si _{1-x} Ge _x alloys studied by spin-polarized photoemission. Physical Review B, 2013, 88, .	3.2	17
116	O-band quantum-confined Stark effect optical modulator from Ge/Si _{0.15} Ge _{0.85} quantum wells by well thickness tuning. Journal of Applied Physics, 2014, 116, .	2.5	17
117	Magnetotransport in Bi ₂ Se ₃ thin films epitaxially grown on Ge(111). AIP Advances, 2018, 8, 115125.	1.3	17
118	Mid-infrared Integrated Electro-optic Modulator Operating up to 225 MHz between 6.4 and 10.7 μ m Wavelength. ACS Photonics, 2022, 9, 249-255.	6.6	17
119	Formation of strain-induced Si-rich and Ge-rich nanowires at misfit dislocations in SiGe: A model supported by photoluminescence data. Applied Physics Letters, 2004, 84, 2895-2897.	3.3	16
120	Crystallinity and microstructure in Si films grown by plasma-enhanced chemical vapor deposition: A simple atomic-scale model validated by experiments. Applied Physics Letters, 2009, 94, 051904.	3.3	16
121	Ge/SiGe superlattices for nanostructured thermoelectric modules. Thin Solid Films, 2013, 543, 153-156.	1.8	16
122	Interfacial sharpness and intermixing in a Ge-SiGe multiple quantum well structure. Journal of Applied Physics, 2018, 123, .	2.5	16
123	On-chip Bragg grating waveguides and Fabry-Perot resonators for long-wave infrared operation up to 84 μ m. Optics Express, 2018, 26, 34366.	3.4	16
124	Plasmon-enhanced Ge-based metal-semiconductor-metal photodetector at near-IR wavelengths. Optics Express, 2019, 27, 20516.	3.4	16
125	Matrix effects in SIMS depth profiles of SiGe relaxed buffer layers. Applied Surface Science, 2004, 231-232, 704-707.	6.1	15
126	Analysis of strain relaxation by microcracks in epitaxial GaAs grown on Ge [*] Si substrates. Journal of Applied Physics, 2007, 101, 103519.	2.5	15

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127	Ge/SiGe heterostructures as emitters of polarized electrons. Journal of Applied Physics, 2012, 111, 063916.	2.5	15
128	Enhanced orbital mixing in the valence band of strained germanium. Physical Review B, 2012, 85, .	3.2	15
129	Sharp bends and Mach-Zehnder interferometer based on Ge-rich-SiGe waveguides on SiGe graded buffer. Optics Express, 2015, 23, 30821.	3.4	15
130	Vertical Ge ¹³³ Si Nanowires with Suspended Graphene Top Contacts as Dynamically Tunable Multispectral Photodetectors. ACS Photonics, 2019, 6, 735-742.	6.6	15
131	Composition determination of semiconductor alloys towards atomic accuracy by HAADF-STEM. Ultramicroscopy, 2019, 200, 84-96.	1.9	15
132	Large Rashba unidirectional magnetoresistance in the Fe/Ge(111) interface states. Physical Review B, 2021, 103, .	3.2	15
133	Onset of vertical threading dislocations in Si _{1-x} Ge _x /Si (001) at a critical Ge concentration. APL Materials, 2013, 1, .	5.1	14
134	Optical tailoring of carrier spin polarization in Ge/SiGe multiple quantum wells. Applied Physics Letters, 2013, 102, 012408.	3.3	14
135	Ge/SiGe quantum wells on Si(111): Growth, structural, and optical properties. Journal of Applied Physics, 2014, 116, .	2.5	14
136	(Invited) Three-Dimensional Epitaxial Si _{1-x} Ge _x , Ge and SiC Crystals on Deeply Patterned Si Substrates. ECS Transactions, 2014, 64, 631-648.	0.5	14
137	Spin diffusion in Pt as probed by optically generated spin currents. Physical Review B, 2015, 92, .	3.2	14
138	Disentangling nonradiative recombination processes in Ge micro-crystals on Si substrates. Applied Physics Letters, 2016, 108, .	3.3	14
139	GaAs epilayers grown on patterned (001) silicon substrates via suspended Ge layers. Scientific Reports, 2019, 9, 17529.	3.3	14
140	Field-resolved detection of the temporal response of a single plasmonic antenna in the mid-infrared. Optica, 2021, 8, 898.	9.3	14
141	Ultra-wideband Ge-rich silicon germanium mid-infrared polarization rotator with mode hybridization flattening. Optics Express, 2019, 27, 9838.	3.4	14
142	Strained Si HFETs for microwave applications: state-of-the-art and further approaches. Solid-State Electronics, 2004, 48, 1443-1452.	1.4	13
143	Hydrostatic strain enhancement in laterally confined SiGe nanostripes. Physical Review B, 2013, 88, .	3.2	13
144	Strong quantum-confined Stark effect from light hole related direct-gap transitions in Ge quantum wells. Applied Physics Letters, 2013, 102, .	3.3	13

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145	Modeling the photo-induced inverse spin-Hall effect in Pt/semiconductor junctions. Journal of Applied Physics, 2018, 124, .	2.5	13
146	Thin relaxed SiGe virtual substrates grown by low-energy plasma-enhanced chemical vapor deposition. Journal of Crystal Growth, 2005, 281, 281-289.	1.5	12
147	Fe thin films grown on single-crystal and virtual Ge(001) substrates. Journal of Applied Physics, 2005, 97, 093906.	2.5	12
148	Strain relaxation in epitaxial Ge crystals grown on patterned Si(001) substrates. Scripta Materialia, 2017, 127, 169-172.	5.2	12
149	Doping dependence of the electron spin diffusion length in germanium. APL Materials, 2019, 7, .	5.1	12
150	Spin-dependent direct gap emission in tensile-strained Ge films on Si substrates. Physical Review B, 2015, 92, .	3.2	11
151	Temperature-controlled coalescence during the growth of Ge crystals on deeply patterned Si substrates. Journal of Crystal Growth, 2016, 440, 86-95.	1.5	11
152	Optical generation of pure spin currents at the indirect gap of bulk Si. Applied Physics Letters, 2017, 110, .	3.3	11
153	Effective g factor of 2D holes in strained Ge quantum wells. Journal of Applied Physics, 2018, 123, .	2.5	11
154	Lattice tilt and strain mapped by X-ray scanning nanodiffraction in compositionally graded SiGe/Si microcrystals. Journal of Applied Crystallography, 2018, 51, 368-385.	4.5	11
155	Evolution of the magnetic and electronic properties of ultrathin Cr(001) films. Solid State Communications, 2000, 116, 283-286.	1.9	10
156	High quality SiGe electronic material grown by low energy plasma enhanced chemical vapour deposition. Thin Solid Films, 2004, 459, 37-40.	1.8	10
157	Long wavelength room temperature laser operation of a strained InGaAs/GaAs quantum well structure monolithically grown by metalorganic chemical vapour deposition on a low energy-plasma enhanced chemical vapour deposition graded misoriented Ge/Si virtual substrate. Optical Materials, 2005, 27, 846-850.	3.6	10
158	Structural Homogeneity of nc-Si Films Grown by Low-Energy PECVD. Electrochemical and Solid-State Letters, 2008, 11, P5.	2.2	10
159	Ge/SiGe Superlattices for Thermoelectric Devices Grown by Low-Energy Plasma-Enhanced Chemical Vapor Deposition. Journal of Electronic Materials, 2013, 42, 2030-2034.	2.2	10
160	Ge quantum well optoelectronic devices for light modulation, detection, and emission. Solid-State Electronics, 2013, 83, 92-98.	1.4	10
161	Metastability and relaxation in tensile SiGe on Ge(001) virtual substrates. Journal of Applied Physics, 2014, 116, 113507.	2.5	10
162	Three-dimensional Ge/SiGe multiple quantum wells deposited on Si(001) and Si(111) patterned substrates. Semiconductor Science and Technology, 2015, 30, 105001.	2.0	10

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163	Integration of GaN Crystals on Micropatterned Si(0 0 1) Substrates by Plasma-Assisted Molecular Beam Epitaxy. <i>Crystal Growth and Design</i> , 2015, 15, 4886-4892.	3.0	10
164	<i>In situ</i> ohmic contact formation for n-type Ge via non-equilibrium processing. <i>Semiconductor Science and Technology</i> , 2017, 32, 115006.	2.0	10
165	Wideband Ge-Rich SiGe Polarization-Insensitive Waveguides for Mid-Infrared Free-Space Communications. <i>Applied Sciences (Switzerland)</i> , 2018, 8, 1154.	2.5	10
166	Strain analysis of a Ge micro disk using precession electron diffraction. <i>Journal of Applied Physics</i> , 2019, 126, .	2.5	10
167	Thermal Conductivity Measurement Methods for SiGe Thermoelectric Materials. <i>Journal of Electronic Materials</i> , 2013, 42, 2376-2380.	2.2	9
168	Exceptional thermal strain reduction by a tilting pillar architecture: Suspended Ge layers on Si (001). <i>Materials and Design</i> , 2017, 116, 144-151.	7.0	9
169	Spin-charge interconversion in heterostructures based on group-IV semiconductors. <i>Rivista Del Nuovo Cimento</i> , 2020, 43, 45-96.	5.7	9
170	Characterization of integrated waveguides by atomic-force-microscopy-assisted mid-infrared imaging and spectroscopy. <i>Optics Express</i> , 2020, 28, 22186.	3.4	9
171	2-D hole gas with two-subband occupation in a strained Ge channel: Scattering mechanisms. <i>Thin Solid Films</i> , 2006, 508, 351-354.	1.8	8
172	Quantitative investigation of the influence of carbon surfactant on Ge surface diffusion and island nucleation on Si(100). <i>Physical Review B</i> , 2010, 82, .	3.2	8
173	Controlling the polarization dynamics by strong THz fields in photoexcited germanium quantum wells. <i>New Journal of Physics</i> , 2013, 15, 075004.	2.9	8
174	Reconstruction of crystal shapes by X-ray nanodiffraction from three-dimensional superlattices. <i>Journal of Applied Crystallography</i> , 2014, 47, 2030-2037.	4.5	8
175	Fabrication of mid-infrared plasmonic antennas based on heavily doped germanium thin films. <i>Thin Solid Films</i> , 2016, 602, 52-55.	1.8	8
176	Functionalization of Scanning Probe Tips with Epitaxial Semiconductor Layers. <i>Small Methods</i> , 2017, 1, 1600033.	8.6	8
177	Strain Engineering in Highly Mismatched SiGe/Si Heterostructures. <i>Materials Science in Semiconductor Processing</i> , 2017, 70, 117-122.	4.0	8
178	Ge/SiGe parabolic quantum wells. <i>Journal Physics D: Applied Physics</i> , 2019, 52, 415105.	2.8	8
179	Effective mass measurement: the influence of hole band nonparabolicity in SiGe/Ge quantum wells. <i>Semiconductor Science and Technology</i> , 2007, 22, S191-S194.	2.0	7
180	Defect analysis of hydrogenated nanocrystalline Si thin films. <i>Physica B: Condensed Matter</i> , 2007, 401-402, 519-522.	2.7	7

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181	Power Factor Characterization of Ge/SiGe Thermoelectric Superlattices at 300ÅK. Journal of Electronic Materials, 2013, 42, 1449-1453.	2.2	7
182	Kinetics of multiexciton complex in GaAs quantum dots on Si. Applied Physics Letters, 2013, 102, 053109.	3.3	7
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